Transistors

2.5V Drive Nch MOSFET RTF025N03

Structure

Silicon N-channel MOSFET

Features

- 1) Low On-resistance.
- 2) Space saving, small surface mount package (TUMT3).
- 3) Low voltage drive (2.5V drive).

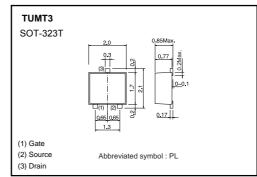
Applications

Switching

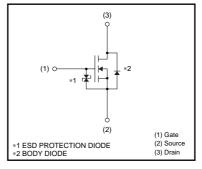
Packaging specifications

	Package	Taping	
Туре	Code	TL	
	Basic ordering unit (pieces)	3000	
RTF025N03	0		

•Dimensions (Unit : mm)



Inner circuit



•Absolute maximum ratings (Ta=25°C)

Parameter		Limits	Unit	
Drain-source voltage		30	V	
Gate-source voltage		12	V	
Continuous	ID	±2.5	А	
Pulsed	I _{DP} *1	±10	А	
Continuous	ls	0.6	А	
Pulsed	I _{SP} *1	10	А	
Total power dissipation		0.8	W	
Channel temperature		150	°C	
Range of storage temperature		-55 to +150	°C	
	Pulsed Continuous Pulsed	Pulsed IDP *1 Continuous Is Pulsed IsP *1 Pulsed IsP *1 PD *2 Tch	VDSS 30 VGSS 12 Continuous Ib ±2.5 Pulsed IDP *1 ±10 Continuous Is 0.6 Pulsed ISP *1 10 Pol sed ISP *1 10 PD *2 0.8 Tch	

∗1 Pw≤10μs, Duty cycle≤1%

*2 Mounted on a ceramic board

Thermal resistance

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Transistors

•Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	lgss	-	-	10	μA	Vgs=12V, Vds=0V
Drain-source breakdown voltage	V(BR) DSS	30	-	-	V	I _D = 1mA, V _{GS} =0V
Zero gate voltage drain current	IDSS	-	-	1	μA	V _{DS} = 30V, V _{GS} =0V
Gate threshold voltage	VGS (th)	0.5	-	1.5	V	V _{DS} = 10V, I _D = 1mA
Static drain-source on-state resistance		-	48	67	mΩ	I _D = 2.5A, V _{GS} = 4.5V
	RDS (on)*	-	50	70	mΩ	I _D = 2.5A, V _{GS} = 4V
		-	70	98	mΩ	I _D = 2.5A, V _{GS} = 2.5V
Forward transfer admittance	Y _{fs} *	2	-	-	S	V _{DS} = 10V, I _D = 2.5A
Input capacitance	Ciss	-	270	_	pF	V _{DS} = 10V
Output capacitance	Coss	-	70	-	pF	V _G s=0V
Reverse transfer capacitance	Crss	-	40	-	pF	f=1MHz
Turn-on delay time	t _{d (on)} *	-	8	-	ns	Vdd≒ 15V
Rise time	tr *	-	15	-	ns	$I_{D}=1.25A$
Turn-off delay time	td (off) *	-	27	_	ns	Vgs= 4.5V Rι=12Ω
Fall time	t _f *	-	11	_	ns	R _G =10Ω
Total gate charge	Qg *	-	3.7	5.2	nC	V _{DD} ≒15V
Gate-source charge	Q _{gs} *	-	0.7	-	nC	V _{GS} = 4.5V
Gate-drain charge	Q _{gd} *	-	1.2	-	nC	I _D = 2.5A

•Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd		-	1.2	V	Is= 0.6A, V _{GS} =0V

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